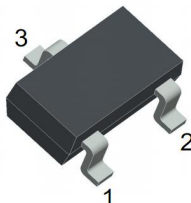
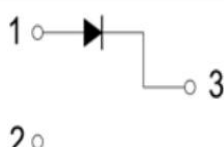
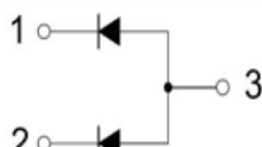
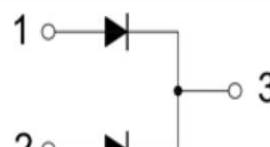
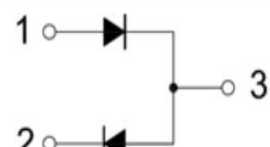


Switching Diodes		SOT-23 Plastic-Encapsulate Diodes																																																					
<u>SOT-23</u> 		Features • High Conductance • Fast Switching Speed • For General Purpose Switching Applications																																																					
MMBD4148A  MARKING:5H	MMBD4148CA  MARKING:D6	MMBD4148CC  MARKING:D5	MMBD4148SE  MARKING:D4																																																				
Solid dot = Green molding compound device, if none,the normal device. Maximum ratings (@Ta=25℃) <table><tr><th>Parameter</th><th>Symbol</th><th>Limit</th><th>Unit</th></tr><tr><td>Non-Repetitive Peak Reverse Voltage</td><td>VRM</td><td>100</td><td>V</td></tr><tr><td>Peak Repetitive Peak Reverse Voltage</td><td>VRRM</td><td>100</td><td>V</td></tr><tr><td>Working Peak Reverse Voltage</td><td>VRWM</td><td>100</td><td>V</td></tr><tr><td>DC Blocking Voltage</td><td>VR</td><td>100</td><td>V</td></tr><tr><td>RMS Reverse Voltage</td><td>VR(RMS)</td><td>72</td><td>V</td></tr><tr><td>Forward Continuous Current</td><td>IFM</td><td>300</td><td>mA</td></tr><tr><td>Average Rectified Output Current</td><td>Io</td><td>200</td><td>mA</td></tr><tr><td>Non-Repetitive Peak Forward Surge Current @t=8.3ms</td><td>IFSM</td><td>2.0</td><td>A</td></tr><tr><td>Power Dissipation</td><td>PD</td><td>350</td><td>mW</td></tr><tr><td>Thermal Resistance from Junction to Ambient</td><td>RθJA</td><td>357</td><td>℃/W</td></tr><tr><td>Junction Temperature</td><td>TJ</td><td>150</td><td>℃</td></tr><tr><td>Storage Temperature Range</td><td>TSTG</td><td>-55~+150</td><td>℃</td></tr></table>				Parameter	Symbol	Limit	Unit	Non-Repetitive Peak Reverse Voltage	VRM	100	V	Peak Repetitive Peak Reverse Voltage	VRRM	100	V	Working Peak Reverse Voltage	VRWM	100	V	DC Blocking Voltage	VR	100	V	RMS Reverse Voltage	VR(RMS)	72	V	Forward Continuous Current	IFM	300	mA	Average Rectified Output Current	Io	200	mA	Non-Repetitive Peak Forward Surge Current @t=8.3ms	IFSM	2.0	A	Power Dissipation	PD	350	mW	Thermal Resistance from Junction to Ambient	RθJA	357	℃/W	Junction Temperature	TJ	150	℃	Storage Temperature Range	TSTG	-55~+150	℃
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Electrical ratings (@Ta=25°C)

Parameter	Symbol	Test Condition	Min	Typ	Max	Unit
Reverse breakdown voltage	V(BR)1	IR=100μA	100			V
	V(BR)2	IR=100μA	75			V
Forward voltage	VF2	IF=10mA			1	V
Reverse current	IR1	VR=75V			5	uA
	IR2	VR=25V			25	nA
Capacitance between terminals	Ctot	VR=0V,f=1MHz			4	PF
Reverse recovery time	t _{rr}	IF=IR=10mA,VR=6V I _{rr} =0.1×IR,RL= 100 Ω			4	nS

Typical Characteristics

